

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

MCH3374 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Ultrahigh-spees switching
- · 1.8V drive

Specifications

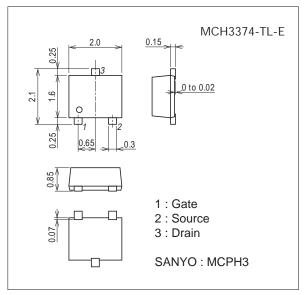
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	VGSS		±8	V
Drain Current (DC)	ID		-3	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-12	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity $< 200V^*$ ", so please take care when handling.

Package Dimensions

unit : mm (typ) 7019A-003

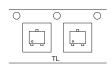


Product & Package Information

• Package : MCPH3

JEITA, JEDEC : SC-70, SOT-323
 Minimum Packing Quantity : 3,000 pcs./reel

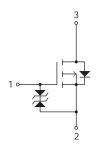
Packing Type: TL



Marking



Electrical Connection



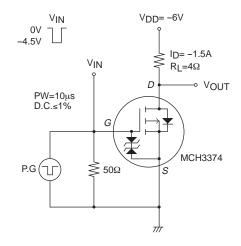
^{*} Machine Model

MCH3374

Electrical Characteristics at Ta=25°C

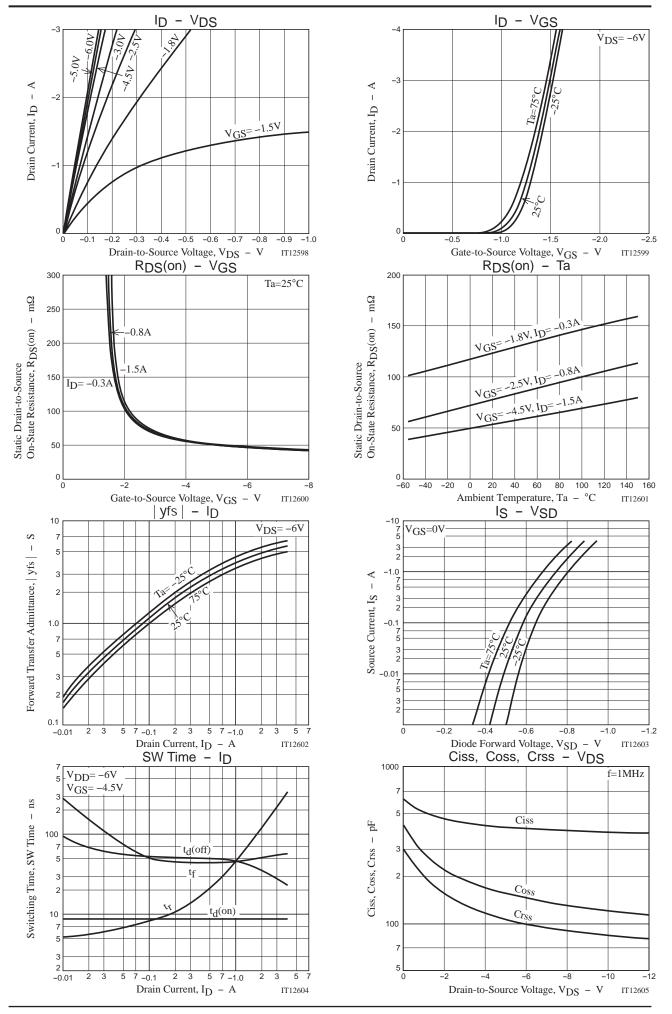
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Symbol Conditions		typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±6.4V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V	
Forward Transfer Admittance	yfs	V _D S=-6V, I _D =-1.5A	2.7	4.5		S	
	R _{DS} (on)1	I _D =-1.5A, V _G S=-4.5V		54	70	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =-0.8A, V _G S=-2.5V		80	115	mΩ	
	R _{DS} (on)3	I _D =-0.3A, V _G S=-1.8V			215	mΩ	
Input Capacitance	Ciss			405		pF	
Output Capacitance	Coss	V _{DS} =-6V, f=1MHz		145		pF	
Reverse Transfer Capacitance	Crss			100		pF	
Turn-ON Delay Time	t _d (on)			8.8		ns	
Rise Time	t _r	Considered Took Circuit		80		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		41		ns	
Fall Time	tf			50		ns	
Total Gate Charge	Qg			5.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-3A		0.7		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		1.6		nC	
Diode Forward Voltage	V _{SD}	I _S =-3A, V _G S=0V		-0.85	-1.2	V	

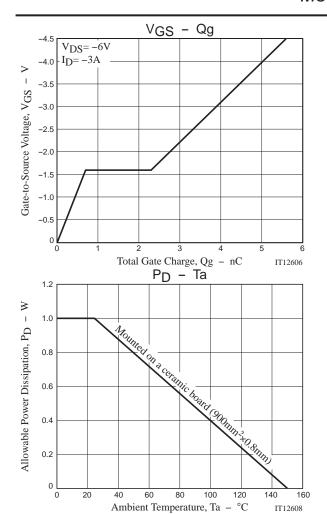
Switching Time Test Circuit

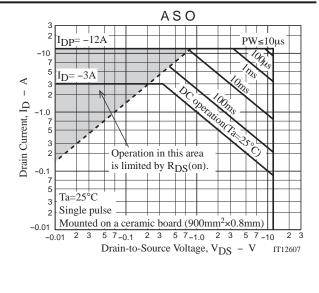


Ordering Information

Device	Package	Shipping	memo	
MCH3374-TL-E	MCPH3	3,000pcs./reel	Pb Free	





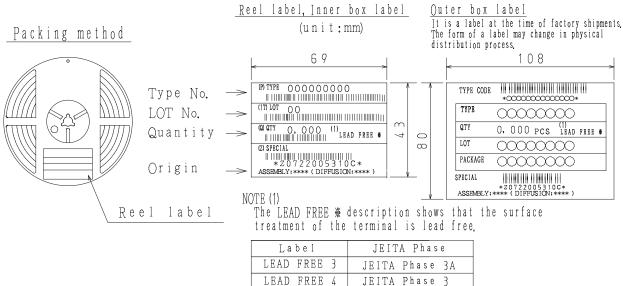


Taping Specification

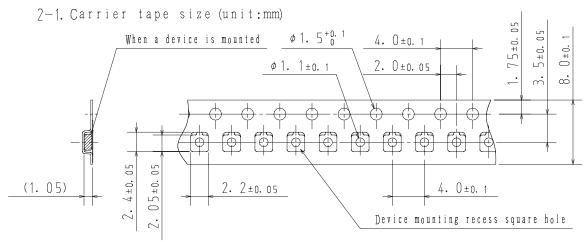
MCH3374-TL-E

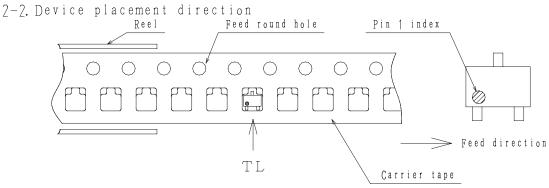
1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
мсрн3	мсрн3	3,000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



2. Taping configuration

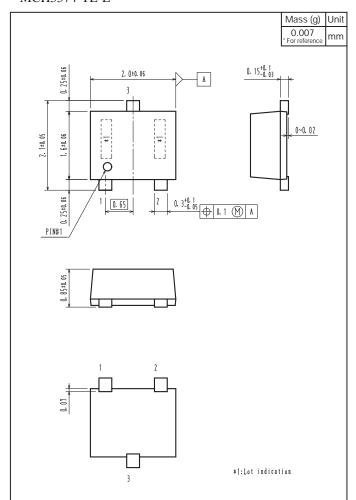




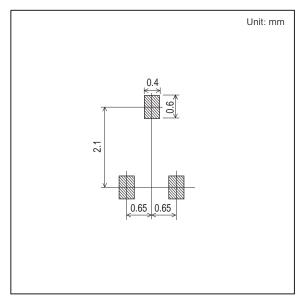
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

MCH3374-TL-E



Land Pattern Example



Note on usage: Since the MCH3374 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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